



SPECIFICATIONS

- ELECTRICAL: NPN SILICON TRANSISTOR *RCA 2N3879* FAMILY OR EQUIV.
 - A. $V_{CE\text{ER}} \text{ sus. } R_{BE} = 50 \text{ OHMS, } I_C = 200 \text{ MA}$ 90V MIN.
 - B. V_{CB0} 120V MIN.
 - C. $H_{FE} @ V_{CE} = 5V I_C = 500 \text{ MA}$ 40 MIN.
 - D. $\theta_{JC} \text{ MAX.}$ 5.0 C/W MAX.
 - E. $I_{S/b} @ V_{CE} = 40V,$ 500 MA

FALL CHARACTERISTICS TO BE THOSE OF BASIC FAMILY.

- MECHANICAL: PER MAX. DIMENSIONS & SHAPE SHOWN HERE.
- MARKING: STAMP TOP OF CASE AS FOLLOWS: FBN-L209
- LEADS: HOT SOLDER DIPPED
- To protect against damage due to electrostatic discharge, these units must be manufactured, handled and shipped in accordance with DOD-STD-1686.

ISSUE:		
A	ORIGINAL	5/9/79
B	ADDED NOTE 5, PER ECo #A01987 12	3-5-87

LES-F		
USED ON	DWG.	
APPL'S		
DR. K.R.	CH. ENG. [Signature]	
MATERIAL: 5/15/79		
FINISH:		
UNLESS OTHERWISE SPECIFIED DIMENSIONS ARE IN INCHES & TOLERANCES ARE: DEC. ±.005 FRACTIONS: ±1/64 ANGLES ±1/2°		
TITLE: TRANSISTOR		
SCALE:		
LAMBDA ELECTRONICS CORP. NEW YORK		
SIZE B	LAMBDA PART NO. & DWG. NO. FBN-L209	REV B

SHEET